



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s):

Raul-Adrian Cernea and Yan Li

Title:

Non-Volatile Memory and Method With Improved Sensing

Application No.:

10/665,828

Filing Date:

September 17, 2003

Examiner:

David Lam

Group Art Unit:

2818

Docket No.:

SNDK.268US1

Conf. No.:

6022

Certificate of Mailing Under 37 CFR 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on _ May 26, 2004

Signature

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Pursuant to 37 C.F.R. §§ 1.56, 1.97 and 1.98, Applicant(s) call(s) the documents listed on the enclosed Form PTO-1449 to the Examiner's attention in this patent application.

This application has a filing date after June 30, 2003. Copies of the U.S Patent(s) and U.S. Published Patent Application(s) documents listed on the accompanying Form PTO-1449 are not enclosed.

Citation of these documents shall not be construed as (1) an admission that the documents are prior art with respect to the invention or inventions claimed in this application, (2) a representation that a search has been made (other than as indicated by any cited

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Attorney Docket No.: **SNDK.268US1**

Application No.: 10/665,828

document), or (3) an admission that the cited information is, or is considered to be, material to patentability as defined in § 1.56(b).

This information disclosure statement is submitted under 37 C.F.R. § 1.97(c). A check including \$180.00 for the information disclosure statement fee under 37 C.F.R. § 1.17(p), is enclosed. The Commissioner is authorized, however, to charge any fee that may be required, or to credit any overpayment, against Deposit Account No. 502664. This form is being submitted in duplicate.

Respectfully submitted,

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U.S. Depar	tment of	Commerce, Patent	and Trademark	Atty. Docket No.			Application No.	
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PADEMARY	7		U.S. P	atent Documents				
Examinei		Document	Dete	Name	Class	Subclass	Filing I	
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	_1	-L	Foreign	Patent Documents				
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	T	Document	Date	Country	Class	Subclass	Yes	No
	9	·1134746 A2	Sep. 19, 2001	Europe				
	10	WO 02/069340	Sep. 6, 2002	WIPO				1
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	12	2 Eitan et al., "NROM: A Novel Localized Trapping 2-Bit Nonvolatile Memory Cell," IEEE Electron Device Letters, vol. 21, no. 11, Nov. 2000, pp. 543-545						
Examiner	1	<u> </u>	Daté Considere	d				
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